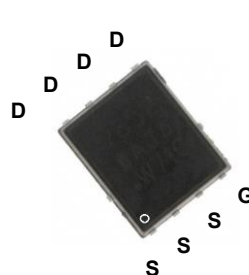
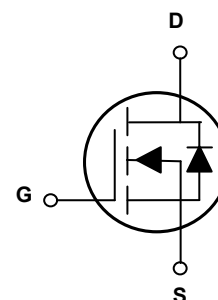


Main Product Characteristics

BV_{DSS}	80V
$R_{DS(ON)}$	3.5mΩ
I_D	130A



PPAK5x6



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSFP08130 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	+20/-12	V
Drain Current-Continuous ($T_C=25^{\circ}C$)	I_D	130	A
Drain Current-Continuous ($T_C=100^{\circ}C$)		82	A
Drain Current-Pulsed ¹	I_{DM}	520	A
Single Pulse Avalanche Energy ²	E_{AS}	400	mJ
Single Pulse Avalanche Current ²	I_{AS}	90	A
Power Dissipation ($T_C=25^{\circ}C$)	P_D	142	W
Power Dissipation-Derate Above 25°C		1.13	W/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.88	°C/W
Storage Temperature Range	T_{STG}	-50 To +150	°C
Operating Junction Temperature Range	T_J	-50 To +150	°C

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	80	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=80V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	-	-	1	μA
		$V_{DS}=64V, V_{GS}=0V, T_J=85^{\circ}\text{C}$	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	2.9	3.5	m Ω
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=5A$	-	19	-	S
Dynamic and Switching Characteristics						
Total Gate Charge ^{3,4}	Q_g	$V_{DS}=40V, I_D=70A, V_{GS}=10V$	-	95.5	143	nC
Gate-Source Charge ^{3,4}	Q_{gs}		-	23.5	35	
Gate-Drain Charge ^{3,4}	Q_{gd}		-	32	48	
Turn-On Delay Time ^{3,4}	$t_{d(on)}$	$V_{DD}=40V, R_G=6\Omega, V_{GS}=10V, I_D=70A$	-	22	33	nS
Rise Time ^{3,4}	t_r		-	15	23	
Turn-Off Delay Time ^{3,4}	$t_{d(off)}$		-	40	60	
Fall Time ^{3,4}	t_f		-	19	29	
Input Capacitance	C_{iss}	$V_{DS}=40V, V_{GS}=0V, F=1\text{MHz}$	-	5510	8265	pF
Output Capacitance	C_{oss}		-	1200	1800	
Reverse Transfer Capacitance	C_{rss}		-	70	100	
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	1.5	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current	I_S	$V_G=V_D=0V, \text{Force Current}$	-	-	130	A
Pulsed Source Current	I_{SM}		-	-	260	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1A, T_J=25^{\circ}\text{C}$	-	-	1	V
Reverse Recovery Time	T_{rr}	$V_R=50V, I_S=10A, di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	-	65	-	nS
Reverse Recovery Charge	Q_{rr}		-	130	-	nC

Note:

1. Repetitive rating: Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=90A, R_G=25\Omega, \text{starting } T_J=25^{\circ}\text{C}$.
3. Pluse test: pulse width $\leq 300\mu s, \text{duty cycle } \leq 2\%$.
4. Essentially independent of operation temperature.

Typical Electrical and Thermal Characteristic Curves

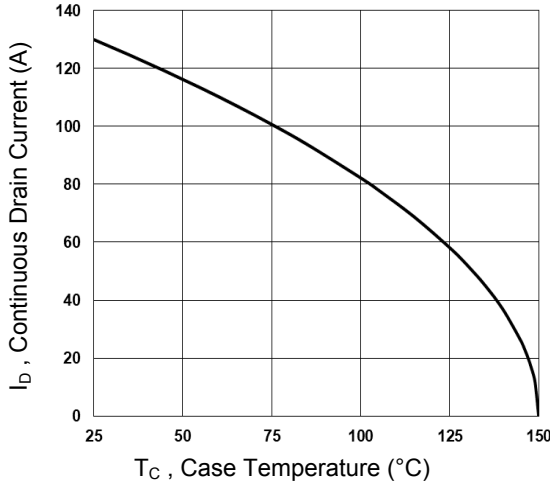


Fig.1 Continuous Drain Current vs. T_C

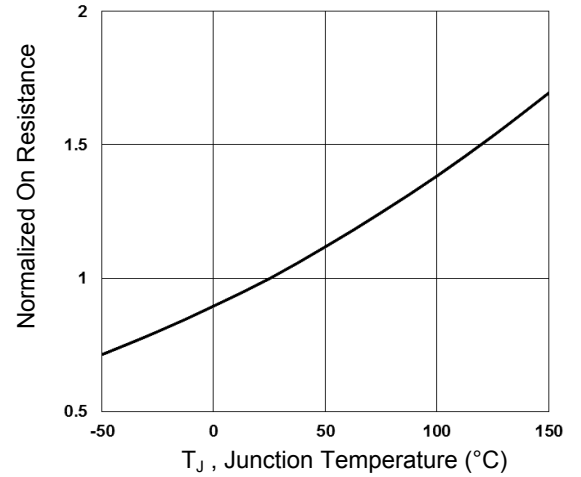


Fig.2 Normalized $R_{DS(ON)}$ vs. T_J

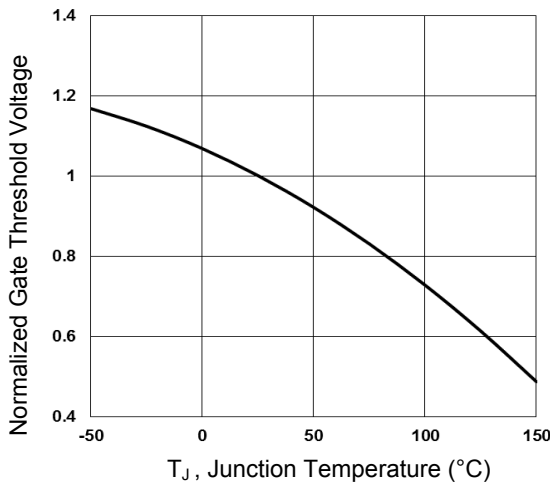


Fig.3 Normalized V_{th} vs. T_J

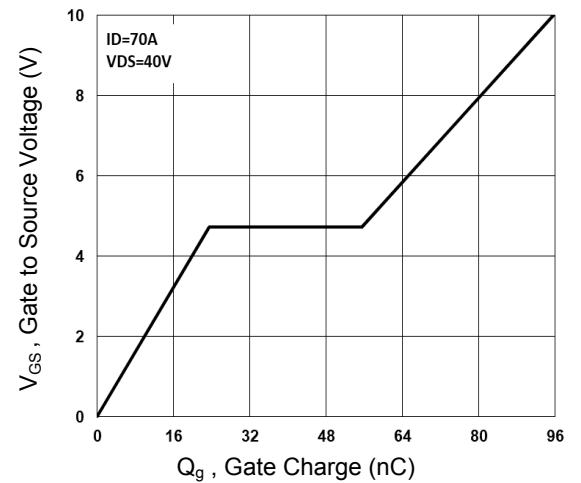


Fig.4 Gate Charge Characteristics

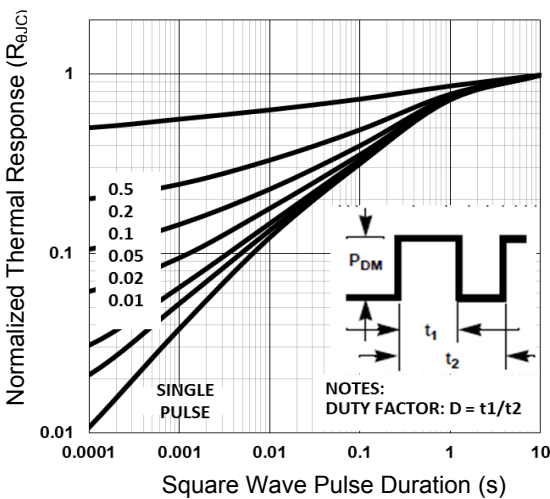


Fig.5 Normalized Transient Impedance

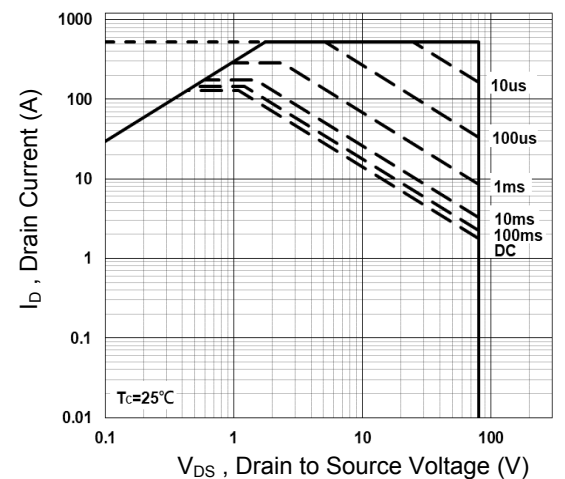


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

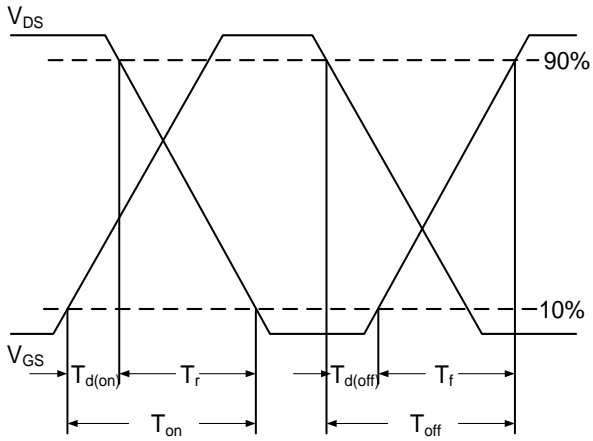


Fig.7 Switching Time Waveform

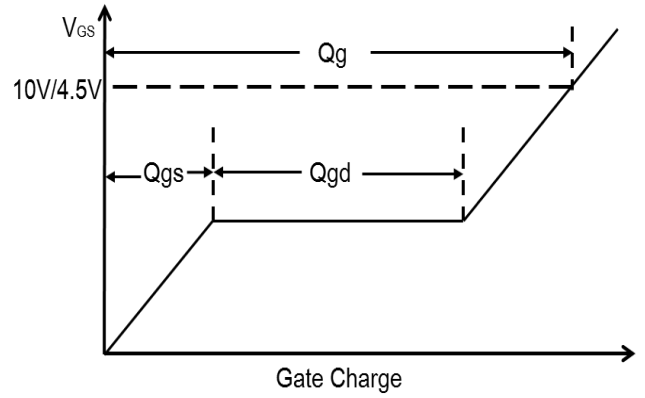
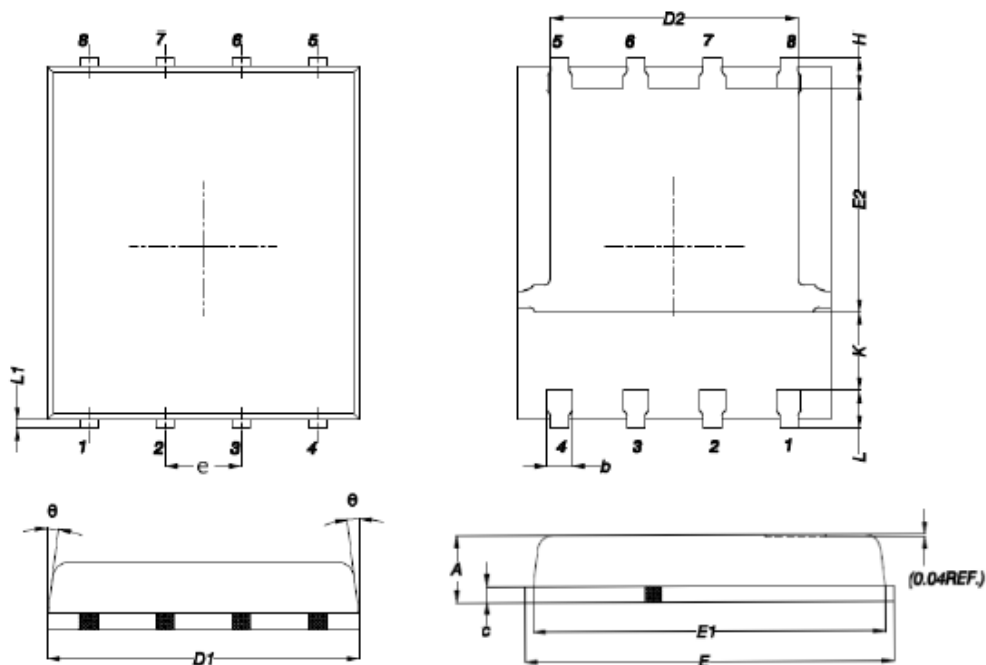


Fig.8 Gate Charge Waveform

Package Outline Dimensions

PPAK5x6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.200	0.850	0.047	0.031
b	0.510	0.300	0.020	0.012
C	0.300	0.200	0.012	0.008
D1	5.400	4.800	0.212	0.189
D2	4.310	3.610	0.170	0.142
E	6.300	5.850	0.248	0.230
E1	5.960	5.450	0.235	0.215
E2	3.920	3.300	0.154	0.130
e	1.27BSC		0.05BSC	
H	0.650	0.380	0.026	0.015
K	-	1.100	-	0.043
L	0.710	0.380	0.028	0.015
L1	0.250	0.050	0.009	0.002
θ	12°	0°	12°	0°